

HIGH-SPEED 4K x 8 FourPort™ STATIC RAM

Features

- High-speed access
 - Commercial: 20ns (max.)
- Low-power operation
 - IDT7054L Active: 750mW (typ.) Standby: 1.5mW (typ.)
- True FourPort memory cells which allow simultaneous access of the same memory locations
- Fully asynchronous operation from each of the four ports: P1, P2, P3, and P4
- TTL-compatible; single 5V (±10%) power supply
- Available in 128 pin Thin Quad Flatpack package

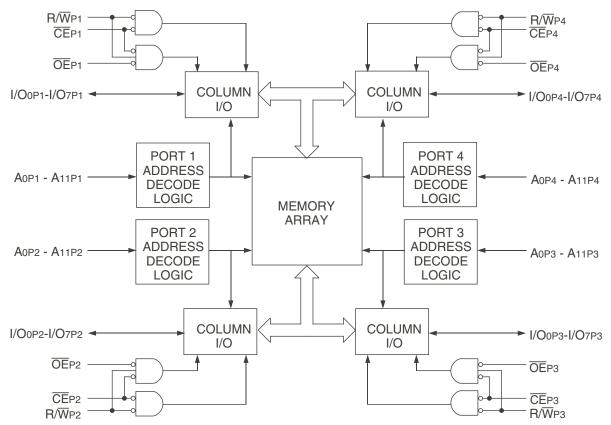
Description

The IDT7054 is a high-speed 4K x 8 FourPort™ Static RAM designed to be used in systems where multiple access into a common RAM is required. This FourPort Static RAM offers increased system performance in multiprocessor systems that have a need to communicate in real time and also offers added benefit for high-speed systems in which multiple access is required in the same cycle.

The IDT7054 is also designed to be used in systems where on-chip hardware port arbitration is not needed. This part lends itself to those systems which cannot tolerate wait states or are designed to be able to externally arbitrated or withstand contention when all ports simultaneously access the same FourPort RAM location.

The IDT7054 provides four independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for

Functional Block Diagram



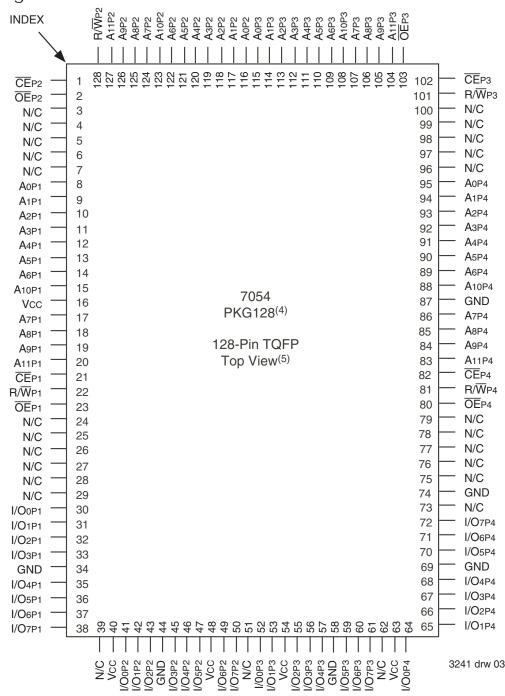
3241 drw 01

reads or writes to any location in memory. It is the user's responsibility to ensure data integrity when simultaneously accessing the same memory location from all ports. An automatic power downfeature, controlled by $\overline{\text{CE}}$, permits the on-chip circuitry of each port to enter a very low power standby power mode.

Fabricated using CMOS high-performance technology, this FourPort SRAM typically operates on only 750mW of power.

The IDT7054 is packaged in a 128-pin Thin Quad Flatpack (TQFP).

Pin Configuration(1,2,3)



- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. Package body is approximately 14mm x 20mm x 1.4mm.
- This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking

Pin Configurations (1,2)

Symbol	Pin Name				
A0 P1 - A11 P1	Address Lines - Port 1				
A0 P2 - A11 P2	Address Lines - Port 2				
A0 P3 - A11 P3	Address Lines - Port 3				
A0 P4 - A11 P4	Address Lines - Port 4				
VO0 P1 - VO7 P1	Data I/O - Port 1				
VO0 P2 - VO7 P2	Data I/O - Port 2				
I/O0 P3 - I/O7 P3	Data I/O - Port 3				
VO0 P4 - VO7 P4	Data I/O - Port 4				
R/W P1	Read/Write - Port 1				
R/W P2	Read/Write - Port 2				
R/W P3	Read/Write - Port 3				
R/W P4	Read/Write - Port 4				
GND	Ground				
Œ P1	Chip Enable - Port 1				
Œ P2	Chip Enable - Port 2				
Œ P3	Chip Enable - Port 3				
Œ P4	Chip Enable - Port 4				
OE P1	Output Enable - Port 1				
OE P2	Output Enable - Port 2				
OE P3	Output Enable - Port 3				
OE P4	Output Enable - Port 4				
Vcc	Power				

NOTES:

3241 tbl 01

- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	٧
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

NOTES:

3241 tbl 02

- 1. $VIL \ge -1.5V$ for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0MHz) TQFP ONLY$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = OV	9	pF
Соит	Output Capacitance	Vout = 0V	10	pF

NOTES:

3241 tbl 03

- This parameter is determined by device characterization but is not production tested.
- 3dV references the interpolated capacitance when the input and the output signals switch from 0V to 3V or from 3V to 0V.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient ade Temperature		Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

3241 tbl 04

NOTES:

1. This is the parameter Ta. This is the "instant on" case temperature.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	۰C
Tstg	Storage Temperature	-65 to +150	°С
lout	DC Output Current	50	mA

NOTES:

3241 tbl 05

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,5) (Vcc = 5.0V ± 10%)

						IX20 Only		X25 & Ind		IX35 Only	
Symbol	Parameter	Condition	Versio	n	TYP. ⁽²⁾	Max.	TYP. ⁽²⁾	Max.	TYP. ⁽²⁾	Max.	Unit
ICC1	Operating Power Supply Current (All Ports Active)	CE = V _I L Outputs Disabled	COM'L.	S L	150 150	300 250	150 150	300 250	150 150	300 250	mA
	(All Ports active)	$f = 0^{(3)}$	IND.	S L			150 150	360 300	150 150	360 300	mA
ICC2	Current	$\overline{\text{CE}} = \text{V}_{\text{IL}}$ Outputs Disabled $f = \text{fMAX}^{(4)}$	COM'L.	S L	240 210	370 325	225 195	350 305	210 180	335 290	mA
	(All Ports Active)		I = IMAX`'	IND.	S L			225 195	400 340	210 180	395 330
ISB	Standby Current (All Ports - TTL Level		COM'L.	S L	70 60	95 80	60 50	85 70	40 35	75 60	mA
	Inputs)		IND.	S L			60 50	115 85	40 35	110 80	mA
ISB1	(All Ports - All	$\begin{array}{l} \textbf{All Ports} \\ \overline{\text{CE}} \geq \text{Vcc} - 0.2 \text{V} \\ \overline{\text{Vin}} \geq \text{Vcc} - 0.2 \text{V} \text{ or} \\ \overline{\text{Vin}} \leq 0.2 \text{V, f} = 0^{(3)} \end{array}$	COM'L.	S L	1.5 0.3	15 1.5	1.5 0.3	15 1.5	1.5 0.3	15 1.5	mA
	CMOS Level Inputs)		IND.	S L		_	1.5 0.3	30 4.5	1.5 0.3	30 4.5	mA

3241 tbl 06

NOTES:

- 1. 'X' in part number indicates power rating (S or L).
- 2. Vcc = 5V, Ta = +25°C and are not production tested.
- 3. f = 0 means no address or control lines change.
- 4. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC Test Conditions" of input levels of GND to 3V.
- 5. For the case of one port, divide the appropriate current above by four.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($Vcc = 5.0V \pm 10\%$)

			7054S		70!		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $Vin = 0V$ to Vcc		10	_	5	μΑ
I LO	Output Leakage Current	\overline{CE} = VIH, VOUT = 0V to VCC		10	_	5	μΑ
Vol	Output Low Voltage	IOL = 4mA	_	0.4	_	0.4	٧
Voh	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	٧

NOTE:

1. At Vcc < 2.0V input leakages are undefined.

2674 tbl 07

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

3241 tbl 08

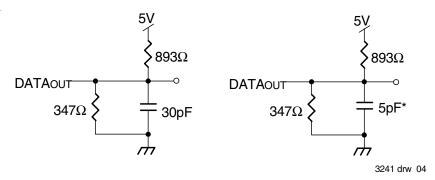
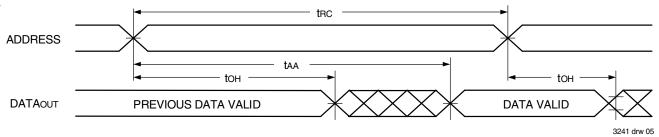


Figure 1. AC Output Test Load

Figure 2. Output Test Load (for tLz, tHz, twz, tow) *Including scope and jig

Timing Waveform of Read Cycle No. 1, Any Port(1)



NOTE:

1. $R/\overline{W} = V_{IH}$, $\overline{OE} = V_{IL}$, and $\overline{CE} = V_{IL}$.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽³⁾

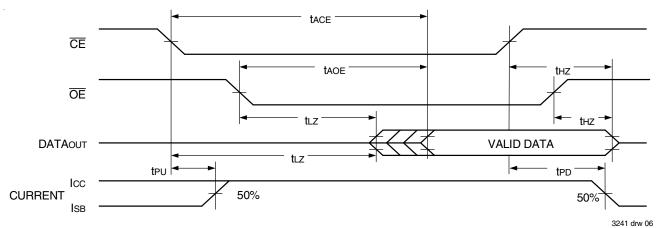
	3 1 11 3 3	7054X20 Com'l Only				7054X35 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	20	_	25	_	35		ns
taa	Address Access Time	_	20	_	25		35	ns
tace	Chip Enable Access Time	_	20	_	25		35	ns
taoe	Output Enable Access Time		10	_	15		25	ns
toн	Output Hold from Address Change	0	_	0		0		ns
tlz	Output Low-Z Time ^(1,2)	5	_	5		5		ns
tHZ	Output High-Z Time ^(1,2)	_	12		15		15	ns
tpu	Chip Enable to Power Up Time ⁽²⁾	0	_	0	_	0		ns
tpD	Chip Disable to Power Down Time ⁽²⁾	_	20		25		35	ns

NOTES:

3241 tbl 09

- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization but is not production tested.
- 3. 'X' in part number indicates power rating (S or L).

Timing Waveform of Read Cycle No. 2, Any Port (1, 2)



- 1. $R/\overline{W} = V_{IH}$ for Read Cycles.
- 2. Addresses valid prior to or coincident with $\overline{\sf CE}$ transition LOW.

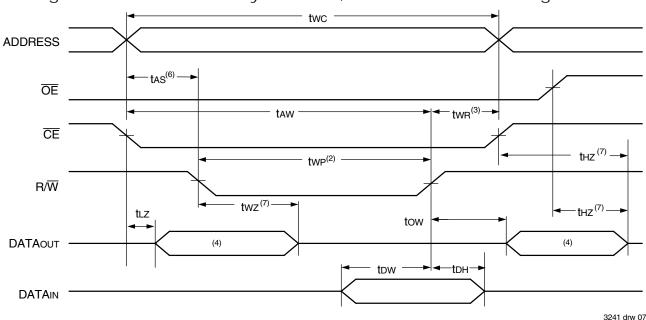
AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

		7054X20 Com'l Only		7054X25 Com'l & Ind		7054X35 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCL	E							
twc	Write Cycle Time	20		25	_	35	_	ns
tew	Chip Enable to End-of-Write	15		20		30		ns
taw	Address Valid to End-of-Write	15		20		30		ns
tas	Address Set-up Time	0		0		0		ns
twp	Write Pulse Width ⁽³⁾	15		20	_	30	_	ns
twr	Write Recovery Time	0		0		0	_	ns
tow	Data Valid to End-of-Write	15		15		20	_	ns
tHZ	Output High-Z Time ^(1,2)		15		15		15	ns
tон	Data Hold Time	0		0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)		12		15		15	ns
tow	Output Active from End-of-Write ^(1,2)	0		0		0		ns
twdd	Write Pulse to Data Delay ⁽⁴⁾		35		45		55	ns
todo	Write Data Valid to Read Data Delay ⁽⁴⁾		30		35		45	ns

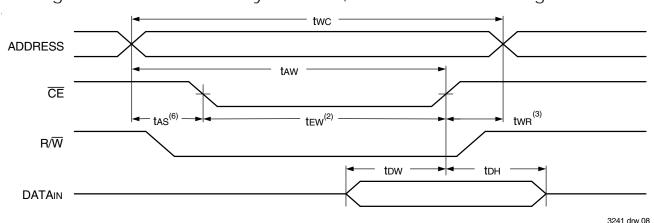
3241 tbl 10

- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization but is not production tested.
- 3. If $\overline{OE} = VIL$ during a \overline{RW} controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off data to be placed on the bus for the required tbw. If $\overline{OE} = VIH$ during an \overline{RW} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp. Specified for $\overline{OE} = VIH$ (refer to "Timing Waveform of Write Cycle", Note 8).
- 4. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read".
- 5. 'X' in part number indicates power rating.

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing (5,8)

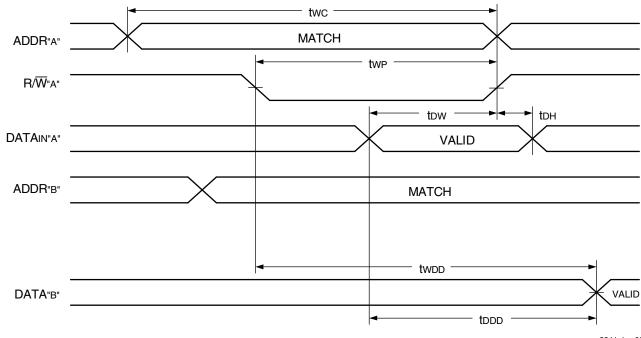


Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)



- 1. R/\overline{W} or \overline{CE} = ViH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a \overline{CE} = V_{IL} and a R/ \overline{W} = V_{IL}.
- 3. two is measured from the earlier of \overline{CE} or $R/\overline{W} = VIH$ to the end of write cycle.
- 4. During this period, the I/O pins are in the output state, and input signals must not be applied.
- 5. If the \overline{CE} LOW transition occurs simultaneously with or after the $\overline{R/W} = V_{IL}$ transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, $\overline{\text{CE}}$ or R/\overline{W} .
- 7. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed but is not production tested.
- 8. If $\overline{OE} = V_{IL}$ during a R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If $\overline{OE} = V_{IH}$ during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

Timing Waveform of Write with Port-to-Port Read^(1, 2)



NOTES:

3241 drw 09

- 1. $\overline{OE} = V_{IL}$ for the reading ports.
- 2. All timing is the same for left and right ports. Port "A" may be either of the four ports and Port "B" is any other port.

Functional Description

The IDT7054 provides four ports with separate control, address, and I/O pins that permit independent access for reads or writes to any location in memory. These devices have an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into standby mode when not selected $(\overline{\text{CE}} = \text{VIH})$. When a port is enabled, access to the entire memory array is permitted. Each port has its own Output Enable control $(\overline{\text{OE}})$. In the read mode, the port's $\overline{\text{OE}}$ turns on the output drivers when set LOW. READ/WRITE conditions are illustrated in the table.

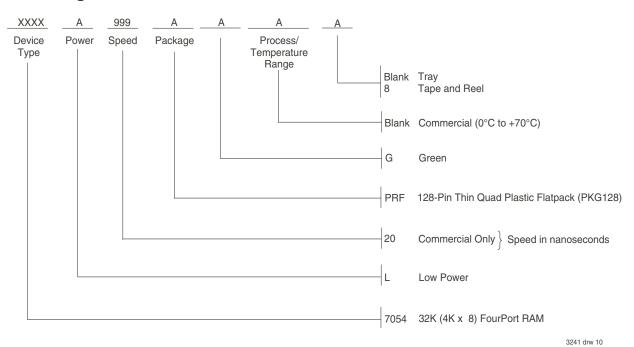
Table I - Read/Write Control

Any Port ⁽¹⁾				
R/W	R/W CE OE D0-7			Function
Χ	Н	Χ	Z	Port Deselected: Power-Down
Х	Н	Χ	Z	CEP1=CEP2=CEP3=CEP4=V⊪ Power Down Mode ISB or ISB1
L	L	Χ	DATAIN	Data on port written into memory (2)
Н	L	L	DATAout	Data in memory output on port
Χ	Χ	Н	Z	Outputs Disabled

3241 tbl 11

- NOTES:
- 1. "H" = VIH, "L" = VIL, "X" = Don't Care, "Z "= High Impedance
- 2. For valid write operation, no more than one port can write to the same address location at the same time.

Ordering Information



NOTE:

1. Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

Ordering Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
20	7054L20PRFG	PKG128	TQFP	С
	7054L20PRFG8	PKG128	TQFP	С

High-Speed 4K x 8 FourPort™ Static RAM Datasheet Document History

01/18/99: Initiated datasheet document history

Converted to new format

Cosmetic typographical corrections

Added additional notes to pin configurations

06/04/99: Changed drawing format

Page 1 Corrected DSC number

09/01/99: Removed Preliminary 11/10/99: Replaced IDT logo

05/23/00: Page 4 Increased storage temperature parameter

Clarified TA parameter

Page 5 DC Electrical parameters-changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes

10/22/01: Page 2 & 3 Added date revision for pin configurations

Page 5, 7 & 8 Added Industrial temp to column heading for 25ns speed to DC & AC Electrical Characteristics

Page 11 Added Industrial temp offering to 25ns ordering information Page 4, 5, 7 & 8 Removed Industrial temp footnote from all tables

Page 6 Changed 5ns to 3ns in AC Test Conditions table

Page 1 & 11 Replaced ${\rm TM}$ logo with ${\rm @}$ logo

02/20/15: Page 1 Added green availability to features

Page 2 Removed IDT in reference to fabrication

Page 2 2V battery backup for Low-power versions are no longer offered

Page 2,3 & 10 The package code PK128-1 changed to PK128 to match standard package codes

Page 10 Added Tape and Reel and Green to Ordering Information

Pages 1-10 Removed all military data including the G108 pin configuration, changed table headings and ordering information

to indicate that there is no longer a military offering for this 7054 device

07/02/18: Product Discontinuation Notice - PDN# SP-17-02

Last time buy expires June 15, 2018

07/11/19: Pages 1 & 10 Deleted obsolete Commercial 25/35ns and Industrial 25ns speed grades

Pages 1 & 10 Removed standard product offering and Industrial speed grade offering

Pages 2 & 10 Updated package code PK128 to PKG128

Page 10 Added Orderable Part Information

04/07/22: Pages 1 - 12 Source file updated to reflect previous Corporate Marketing rebranding

Page 2 Updated the package code

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